

## Polymer-Derived Ceramics and Wireless, Passive Ceramic Strain Sensors

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# Outline

- Motivation
- Objectives
- Material development
- Sensor design and fabrication
- Sensor characterization (on going)

## Summary



## **Motivation – need for wireless strain sensors**





## **Motivation – wireless passive strain sensors**

Parts subjected to severe strain/stress in extreme environments

High temperatures – need passive

Moving parts/hidden areas – need wireless



## **Sensor Classification**

Senor Type	Single Transport	Sensing Mechanisms		
Temperature-	Wired	Semiconducting		
related sensing	Wireless	Temperature-dependent permittivity		
Stress/strain-	Wired	Piezoresistivity		
related sensing	Wireless	Piezodielectricity		
	D	Difficult to develop		



# **Objectives**

Overall Objective

Develop RF resonator-based wireless passive polymer-derived ceramic strain/stress sensors





**Passive Ceramic Sensor** 

#### Scientific Goals

- Develop piezo-dielectric polymer-derived ceramics (pd-PDCs)
- Design and fabricate resonator sensors
- □ Characterize the sensors in extreme environments

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## **Material development – polymer-derived ceramics**



### **Fundamentally Different from Traditional Ceramics**



#### Macro-scale amorphous

- No X-ray diffraction

#### Nano-scale heterogeneity – nanodomain structure

- Two phases: amorphous matrix (AM) and disordered free carbon (FC)
  - Distribution of two phases:
    - Both continuous
    - ✓ AM continuous
    - ✓ FC continuous
  - Possible phase separation within AM phase
- Interface (area) between different phases
- Free volume
- Atomic/molecular scale
  - Large amount of point defects (dangling bonds)
  - Doping effect
  - Residue stresses



Matrix

**Free carbon** 



- Excellent high-temperature properties
- Excellent thermal stability
  - PDCs can be stable up to 1800-2200°C against decomposition and crystalization
- Excellent creep resistance
  - Creep resistance of PDCs can be higher than polycrystalline SiC/Si<sub>3</sub>N<sub>4</sub>
- Excellent oxidation/corrosion resistance
  - Oxidation rate of PDCs is more than 10 times lower than conventional silicon based materials
  - Corrosion rate of PDCs is about 10 times lower than silicon based materials
  - Excellent strength retention



#### Suitable for high-temperature applications



#### Flexible microfabrication capability



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 Amorphous semiconducting behavior at high temperatures – excellent for wired temperature-related sensing















- Material system: SiAlCN
- Polysilazane (VL20): main precursor
- Phenylbis (2,4,6-trimethylbenzoyl) phosphine oxide (819): the photon initiator for UV curing
- Aluminum-tri-sec-butoxide (ASB): source for Al
- Poly (melamine-co-formaldehyde) acrylated solution (PVN): additional source for N
- Methacrylic Acid (MA): for enhancing the effectiveness of UV curing



#### Material system: SiAlCN

Name	MA (wt%)	ASB (wt%)	819 (wt%)	VL20 (wt%)	PVN (wt%)
S-1	2	5	5	78	10
S-2	2	5	5	68	20
S-3	2	5	5	58	30
S-4	5	5	0	90	0
S-5	0	1	0	99	0
S-6	0	5	0	95	0
S-7	0	10	0	90	0
S-8	2	1	0	97	0

#### **Key: lowest dielectric loss**



#### ■ Dielectric properties of SiAlCN at ~ 10 GHz



(a)



(b)

Name	Dielectric constant	Dielectric loss	Frequency (GHz)
S-1	4.87	0.042	9.767
S-2	6.66	0.083	9.743
S-3	7.40	0.21	9.718
S-4	4.45	0.0085	8.826
S-5	3.6	0.0045	9.028
S-6	3.55	0.0046	9.221
S-7	3.85	0.0046	9.337
S-8	4.8	0.0045	9.0035

#### ✓ 819 can cause drastic increase in dielectric loss

✓ Other additives have less effect



Piezodielectricity at 1 MHz



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## **Sensor design and fabrication**



- W<sub>c</sub>: the width of the PDC rectangular  $W_c = \frac{1}{2}L_c$
- $L_c$ : the length of the PDC rectangular –
- H: the thickness of the PDC rectangular
- W<sub>a</sub>: the width of the slot
- L<sub>a</sub>: the length of the slot
- X<sub>a</sub>: the distance of the slot from the edge

#### Low dielectric loss and high Q factor



#### □ The effect of the rectangualar dimensions



 $W_c = 8 \text{ mm}; L_c = 16 \text{ mm}; H = 1 \text{ mm}$ 

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#### □ The effect of the slot dimensions





#### Sensor fabrication

Material: SiAlCN (1%ASB+2%MA+97%VL20)

#### **Fabrication procedure:**

- Cross-link the precursor synthesized in our lab.
- $\circ$  Ball-milling the cross-linked precursor to a fine powder of  $\sim$ 1um scale
- Compress the powder into a disk of 1 inch in diameter and 2-3 mm in thickness using a die under a uniaxial pressure of 50 MPa.
- Further treat the disk under isostatic pressure of 200 MPa at room temperature.
- Pyrolyzed the disk at 1000°C for 4 hrs using a heating rate of 1°C/min.
- Machine the pyrolyzed ceramic disk into the final dimension of the sensor.
- Make electrode on the final sensor.

#### **<u>Final sensor feature</u>**:

 $W_c = 8 \text{ mm}; L_c = 16 \text{ mm}; H = 1 \text{ mm}; Pt \text{ thickness} > 20 \text{ um}$  $W_a = 0.4 \text{ mm}; L_a = 6 \text{ mm}; X_a = 1 \text{ mm}$ 

**Calculated sensor feature:** 

- ✓ Resonant frequency = 9.58 GHz;
- ✓ Q-factor will be 383





# **Sensor characterization (on going)**





# Summary

- Polymer-derived ceramics possess necessary properties for making hightemperature sensors for turbine applications
- Developed piezodielectric SiAlCN ceramics for wireless passive strain/stress sensors for high-temperature applications.
- A wireless passive strain/stress sensor based-on RF cavity resonator has been designed and fabricated.
- The sensor testing is on going.



# Thank you!